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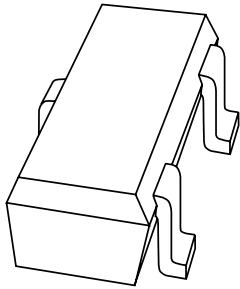
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



1PS193 High-speed diode

Product data sheet
Supersedes data of April 1996

1996 Sep 11

High-speed diode

1PS193

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 80 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

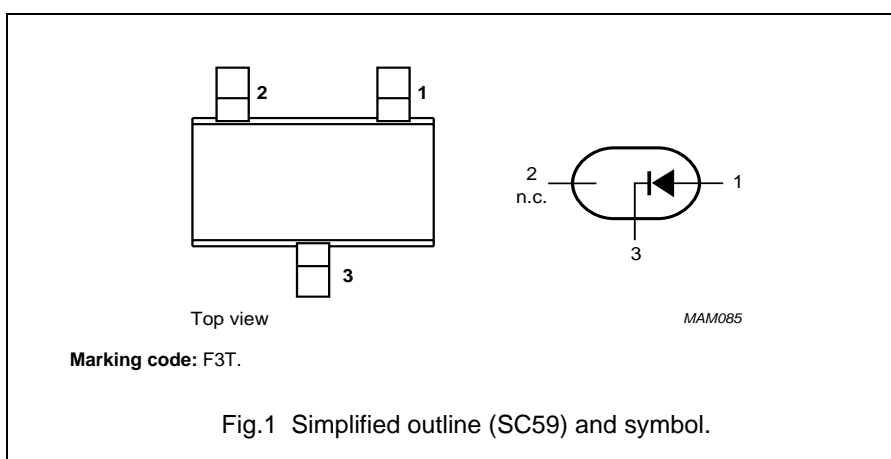
- High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

The 1PS193 is a high-speed switching diode, fabricated in planar technology, and encapsulated in the small plastic SMD SC59 package.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		—	85	V
V_R	continuous reverse voltage		—	80	V
I_F	continuous forward current	see Fig.2; note 1	—	215	mA
I_{FRM}	repetitive peak forward current		—	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge			
		$t = 1\text{ }\mu\text{s}$	—	4	A
		$t = 1\text{ s}$	—	0.5	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	—	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

1PS193

ELECTRICAL CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	see Fig.3 $I_F = 1\text{ mA}$	610	–	mV
		$I_F = 10\text{ mA}$	740	–	mV
		$I_F = 50\text{ mA}$	–	1.0	V
		$I_F = 100\text{ mA}$	–	1.2	V
I_R	reverse current	see Fig.4 $V_R = 25\text{ V}$	–	30	nA
		$V_R = 80\text{ V}$	–	0.5	μA
		$V_R = 25\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$	–	30	μA
		$V_R = 80\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$;	–	100	μA
C_d	diode capacitance	$f = 1\text{ MHz}$; $V_R = 0$; see Fig.5	–	1.5	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$; see Fig.6	–	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\text{ mA}$; $t_p = 20\text{ ns}$; see Fig.7	–	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		250	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

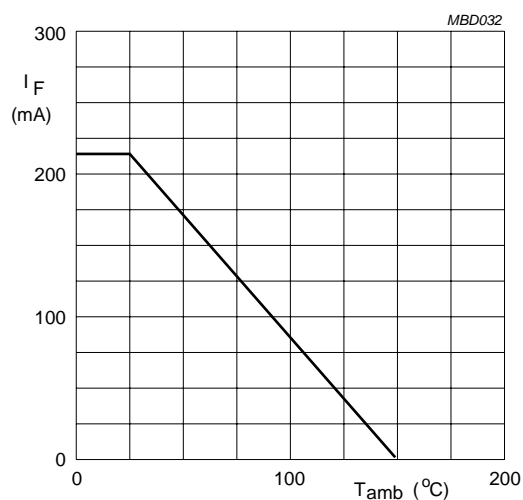
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

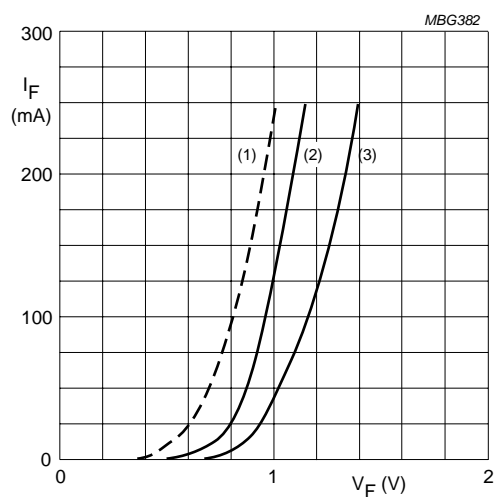
1PS193

GRAPHICAL DATA



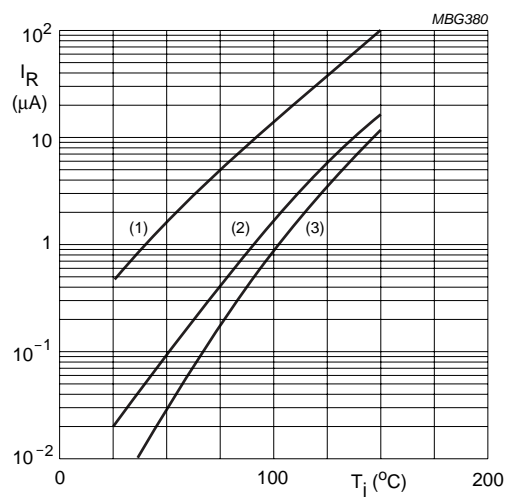
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



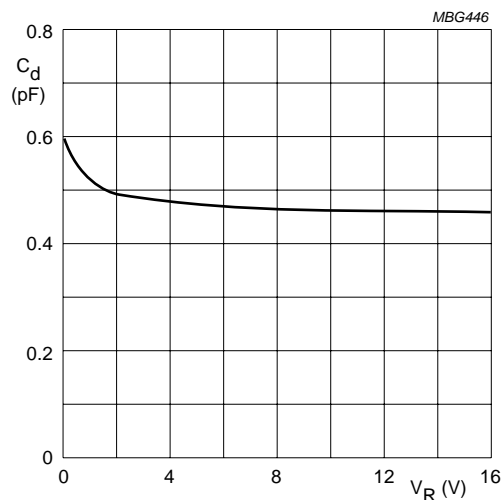
- (1) $T_j = 150^\circ\text{C}$; typical values.
- (2) $T_j = 25^\circ\text{C}$; typical values.
- (3) $T_j = 25^\circ\text{C}$; maximum values.

Fig.3 Forward current as a function of forward voltage.



- (1) $V_R = 80\text{ V}$; maximum values.
- (2) $V_R = 80\text{ V}$; typical values.
- (3) $V_R = 25\text{ V}$; typical values.

Fig.4 Reverse current as a function of junction temperature.

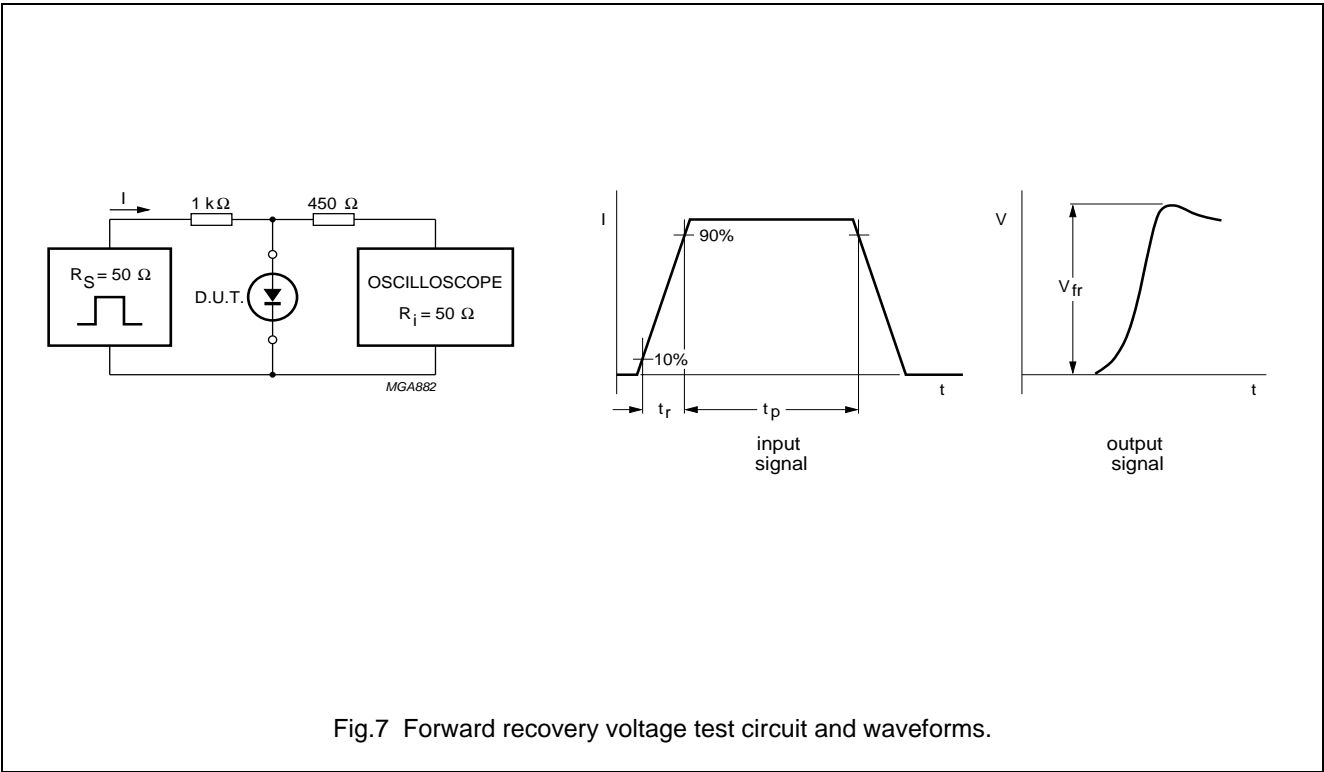
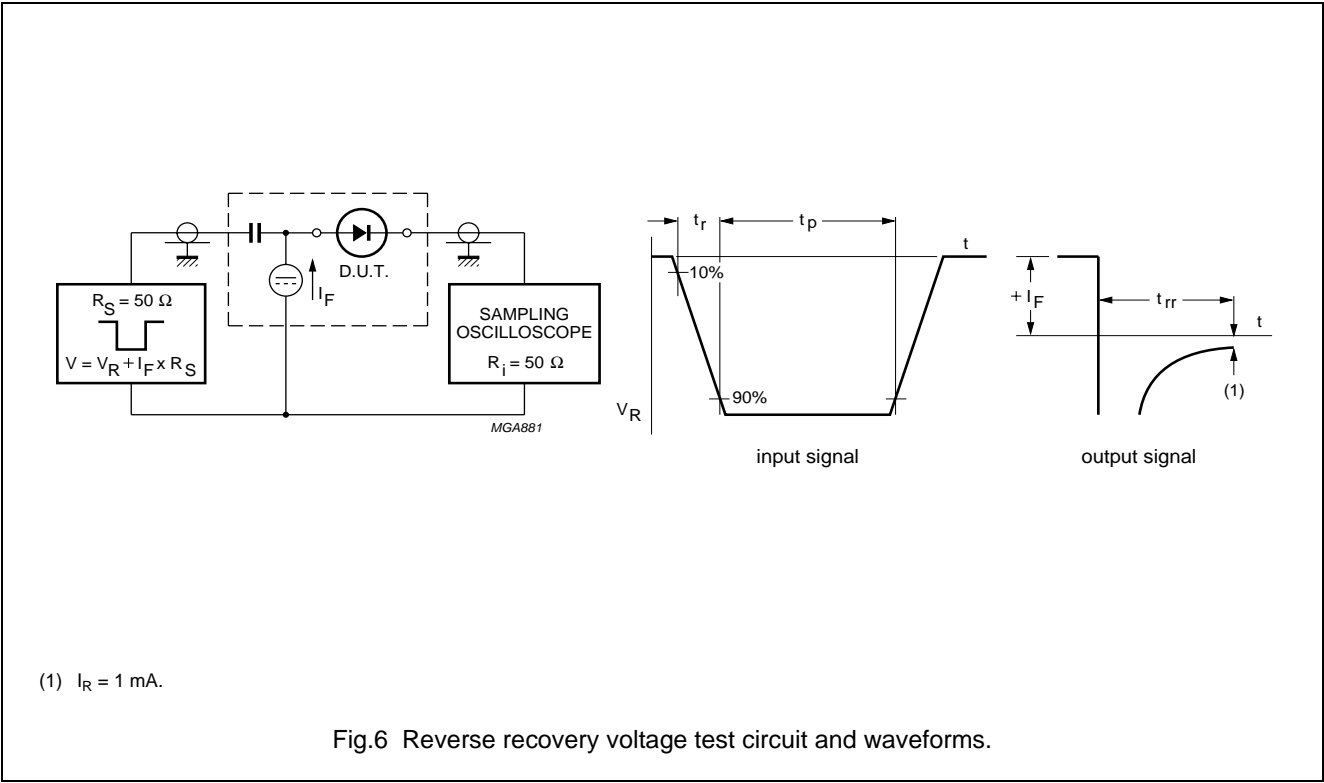


$f = 1\text{ MHz}$; $T_j = 25^\circ\text{C}$.

Fig.5 Diode capacitance as a function of reverse voltage; typical values.

High-speed diode

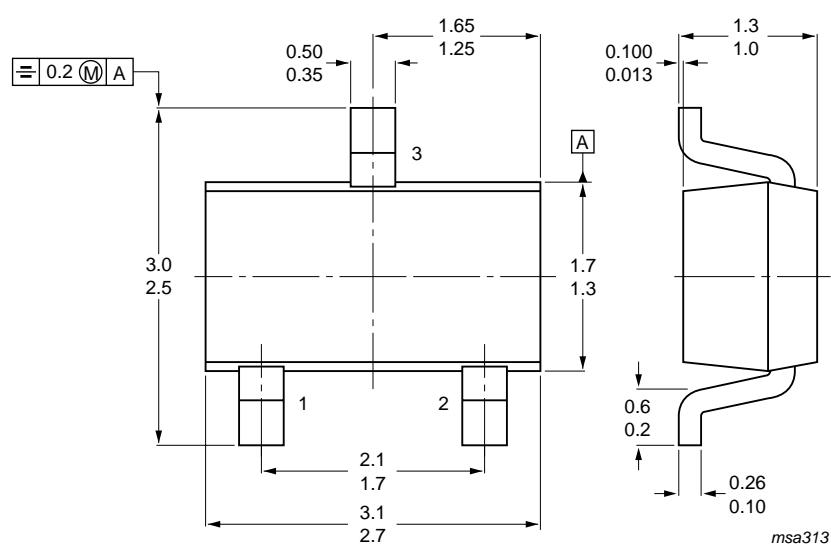
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High-speed diode

1PS193

PACKAGE OUTLINE



Dimensions in mm.

Fig.8 SC59.

High-speed diode

1PS193

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: **<http://www.nxp.com>**

For sales offices addresses send e-mail to: **salesaddresses@nxp.com**

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